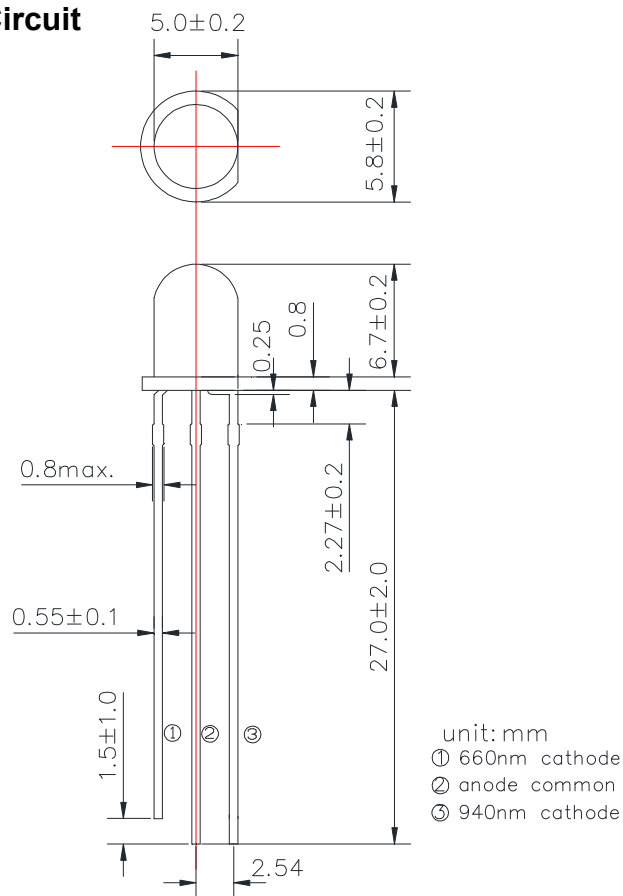


L660N/940D-04A

Multi Wavelength LED

Outline and Internal Circuit



Features

- Chip Material : AlGaInP(660nm) , AlGaAs(940nm)
- Chip Dimension : 350um * 350um
- Number of Chips : 2pcs
- Peak Wavelength : 660 / 940nm typ.
- Lead Frame Die : Silver Plated on Copper
- Package Resin : PA9T Resin
- Lens : Epoxy Resin

Application

660nm

Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Ratings	Unit
Power Dissipation	PD	120	mW
Forward Current	IF	50	mA
Pulse Forward Current	IFP	300	mA
Reverse Voltage	VR	5	V
Thermal Resistance	Rthjs	300	K/W
Junction Temperature	Tj	120	°C
Operating Temperature	Topr	-40 ~ +100	°C
Storage Temperature	Tstg	-40 ~ +100	°C
Soldering Temperature	TSOL	265	°C

‡Pulse Forward Current condition : Duty 1% and Pulse Width=10us.

‡Soldering condition : Soldering condition must be completed with 3 seconds at 265°C.

Optical and Electrical Characteristics (Tc=25°C)

(*: 100% testing, **: reference value)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Forward Voltage	VF		1.9	2.3	V	IF=20mA*
	VFP		3.5			IFP=300mA**
Reverse Current	IR			10	uA	VR=5V*
Total Radiated Power	PO	8.0	12		mW	IF=20mA*
			150			IFP=300mA**
Luminous Flux	Φv		800		mlm	IF=20mA**
Peak Wavelength	λp	650		670	nm	IF=20mA*
Dominant Wavelength	λD		640		nm	IF=20mA**
Half Width	Δλ		16		nm	IF=20mA**
Rise Time	tr		10		ns	IF=20mA**
Fall Time	tf		10		ns	IF=20mA**

‡ Radiated Power is measured by S3584-08.

940nm

Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Ratings	Unit
Power Dissipation	PD	170	mW
Forward Current	IF	100	mA
Pulse Forward Current	IFP	1000	mA
Reverse Voltage	VR	5	V
Thermal Resistance	Rthjs	300	K/W
Junction Temperature	Tj	120	°C
Operating Temperature	Topr	-40 ~ +100	°C
Storage Temperature	Tstg	-40 ~ +100	°C
Soldering Temperature	TSOL	265	°C

‡Pulse Forward Current condition : Duty 1% and Pulse Width=10us.

‡Soldering condition : Soldering condition must be completed with 3 seconds at 265°C.

Optical and Electrical Characteristics (Tc=25°C)

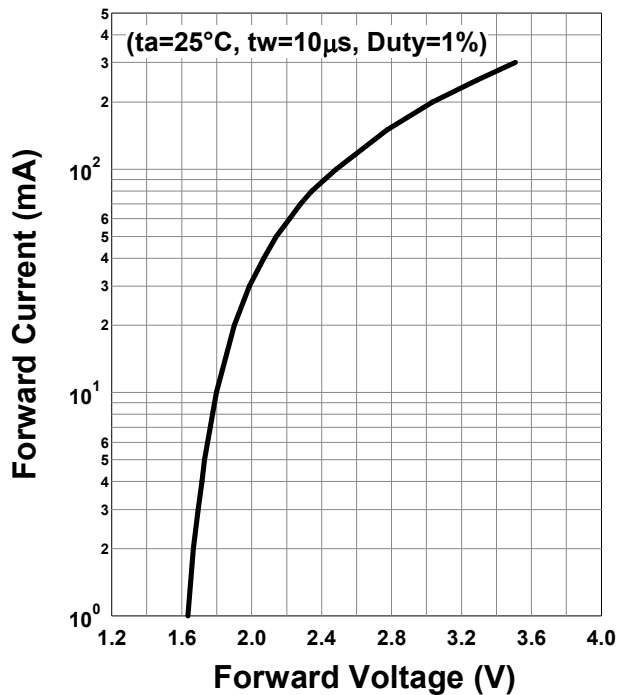
(*: 100% testing, **: reference value)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Forward Voltage	VF		1.3	1.7	V	IF=20mA*
	VFP		2.1			IFP=1A**
Reverse Current	IR			10	uA	VR=5V*
Total Radiated Power	PO	7.0	10		mW	IF=20mA*
			410			IFP=1A**
Peak Wavelength	λ_p	930		955	nm	IF=20mA*
Half Width	$\Delta\lambda$		40		nm	IF=20mA**
Rise Time	tr		10		ns	IF=20mA**
Fall Time	tf		15		ns	IF=20mA**

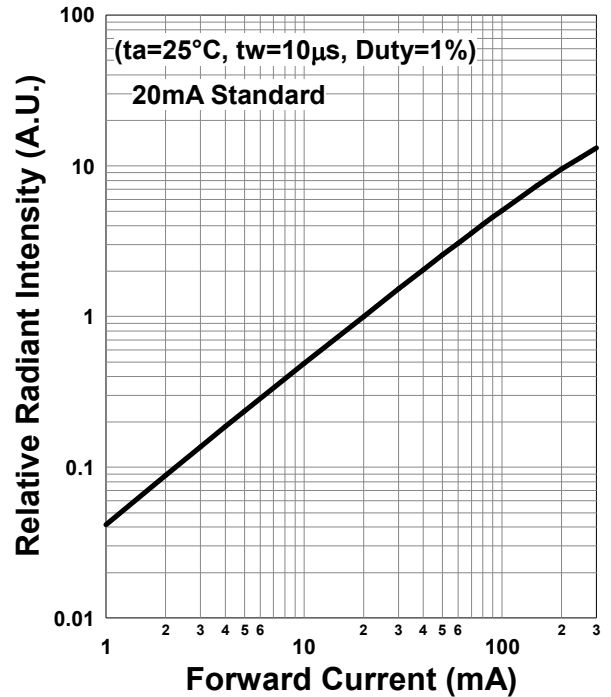
‡ Radiated Power is measured by S3584-08.

Typical Characteristic Curves 660nm

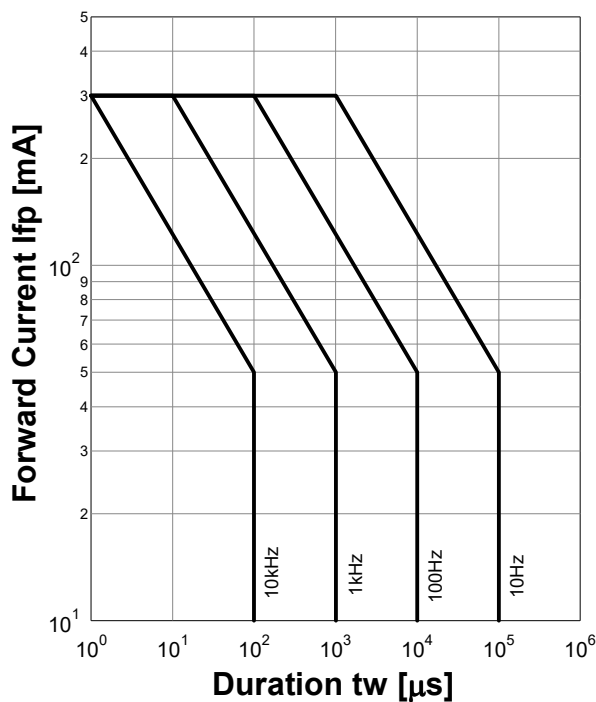
Forward Current - Forward Voltage



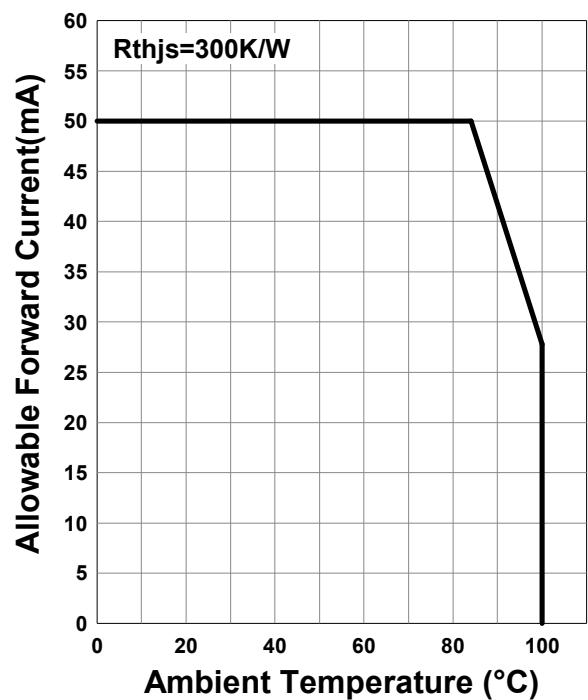
Relative Radiant Intensity - Forward Current



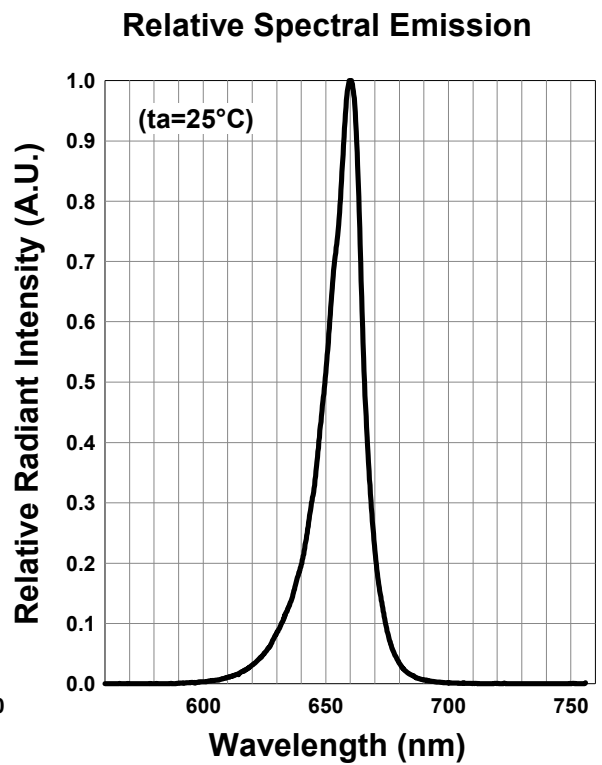
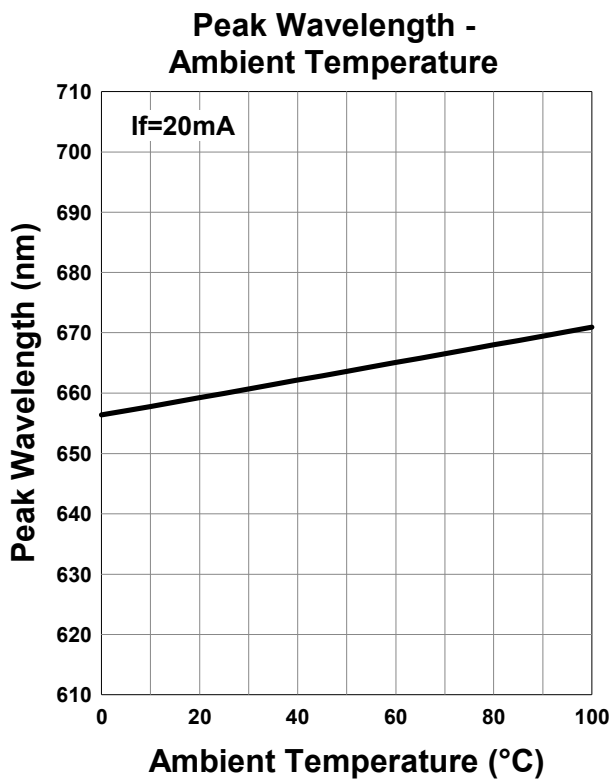
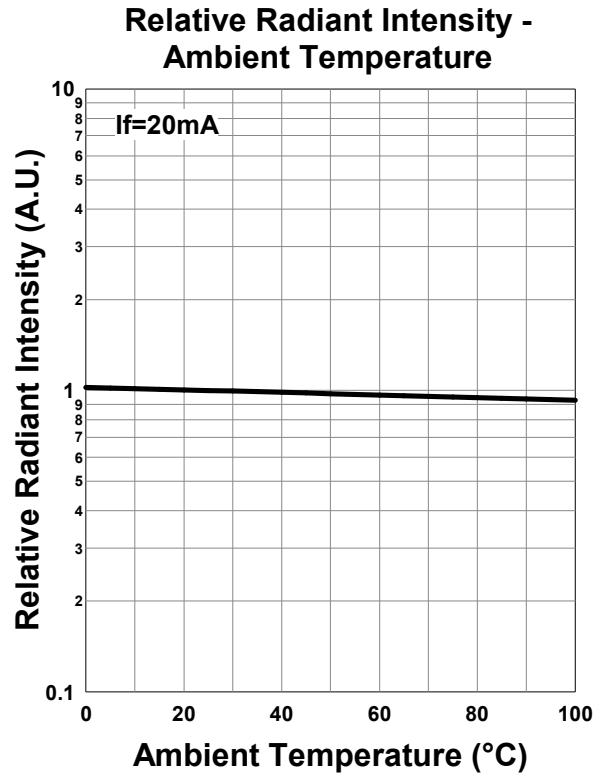
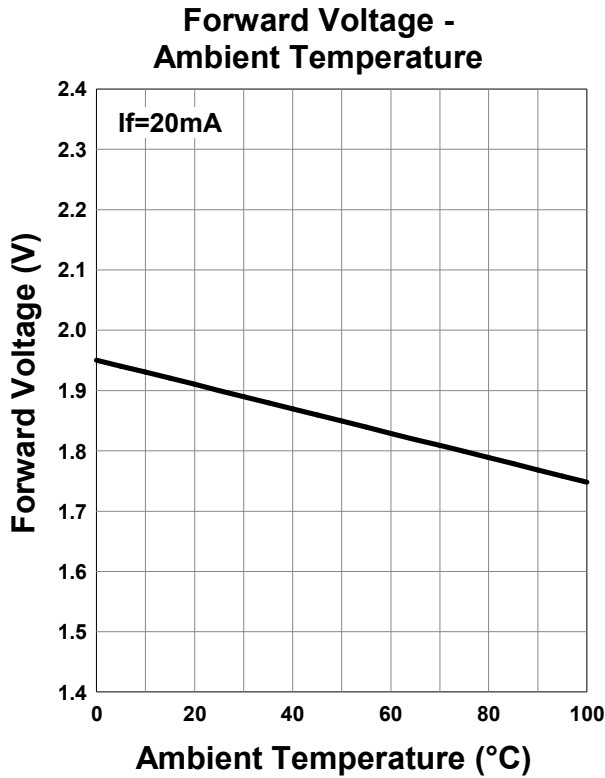
Forward Current - Pulse Duration



Allowable Forward Current - Ambient Temperature

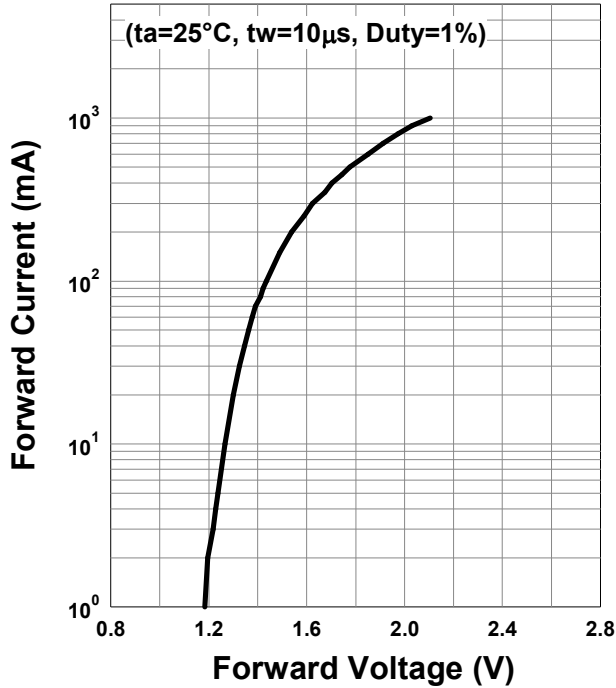


660nm

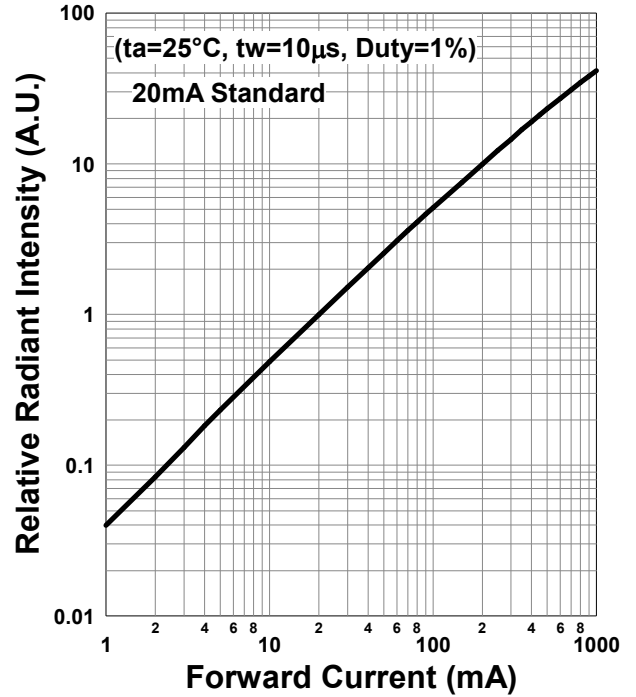


Typical Characteristic
Curves 940nm

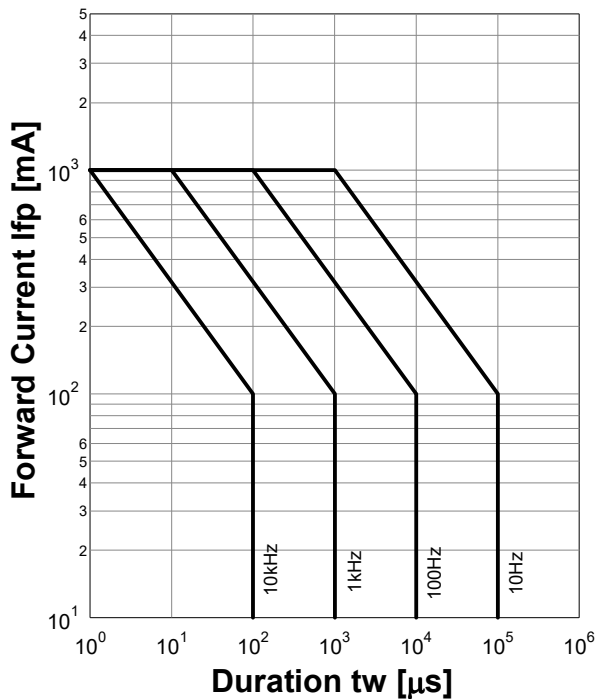
Forward Current - Forward Voltage



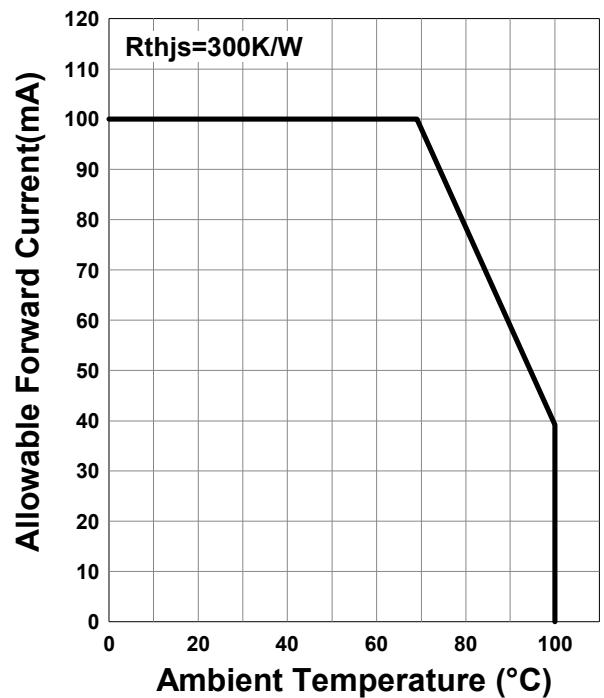
Relative Radiant Intensity - Forward Current



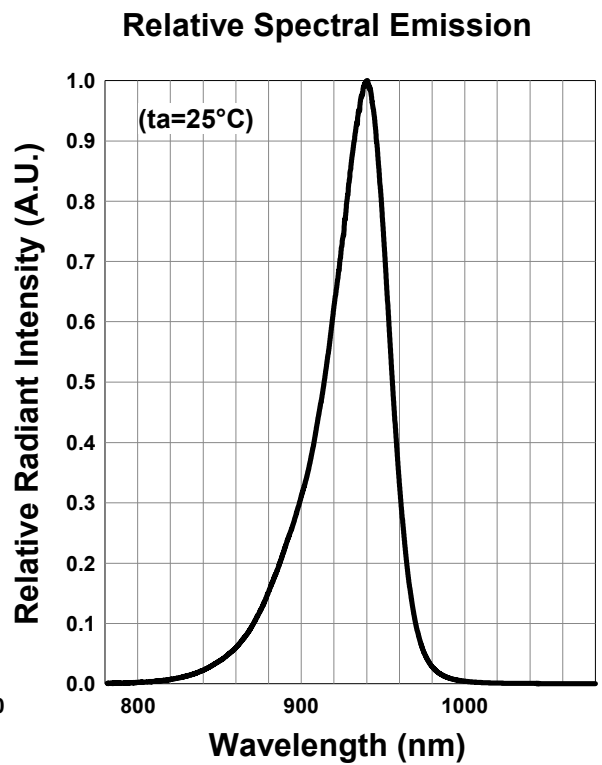
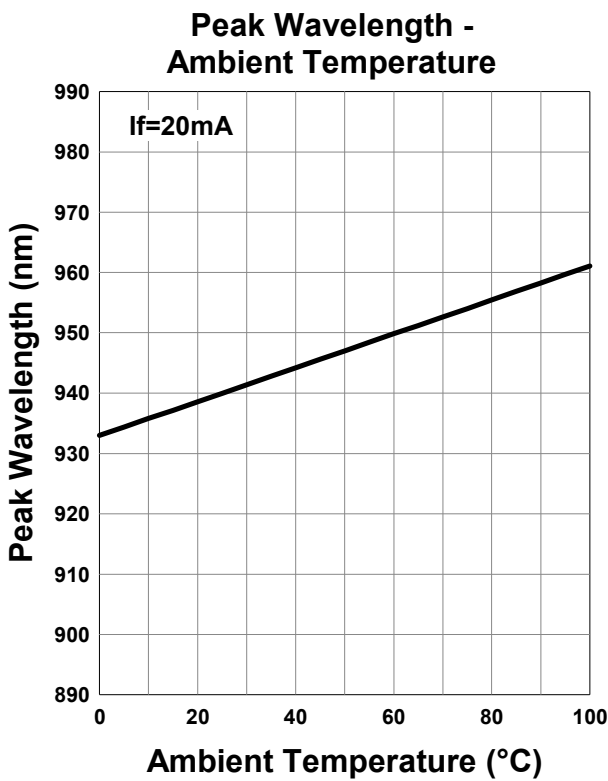
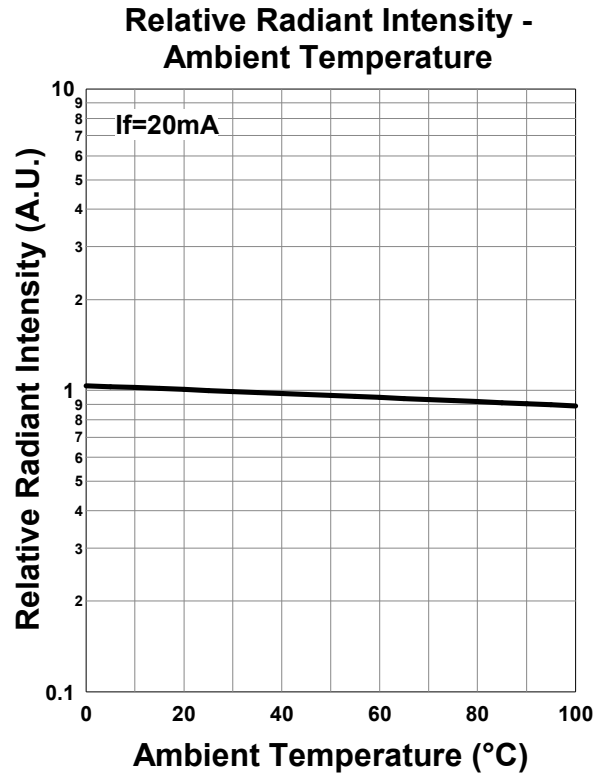
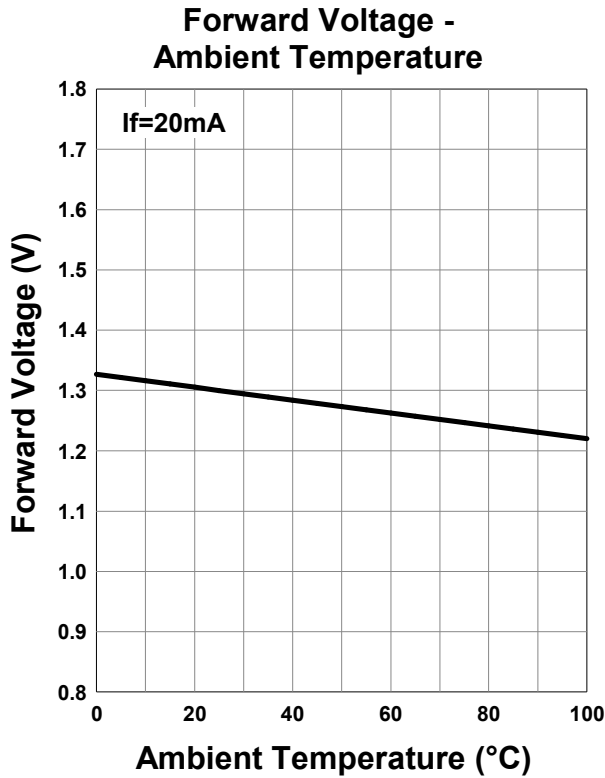
Forward Current - Pulse Duration



Allowable Forward Current - Ambient Temperature



940nm



Disclaimer

Product specifications and data shown in this product catalog are subject to change without notice for the purposes of improving product performance, reliability, design, or otherwise.

Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements.

Product data and parameters may vary by user application and over time.

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